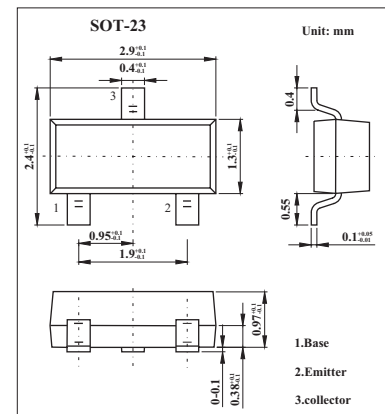


## Silicon PNP Epitaxial

## 2SA1235

## ■ Features

- Small collector to emitter saturation voltage.
- Excellent lineary DC forward current gain.
- Super mini package for easy mounting.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-50	V
Emitter-base voltage	$V_{EBO}$	-6	V
Collector current	$I_C$	-200	mA
Collector dissipation ( $T_a=25^\circ\text{C}$ )	$P_C$	150	mW
Jumction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -100\mu\text{A}$ , $R_{BE} = \infty$	-50			V
Collector cutoff current	$I_{CBO}$	$I_{CB} = -50\text{V}$ , $I_E = 0$			-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -6\text{V}$ , $I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -6\text{V}$ , $I_C = -1\text{mA}$	150		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}$ , $I_B = -10\text{mA}$			-0.3	V
Current gain bandwidth product	$f_T$	$V_{CE} = -6\text{V}$ , $I_E = 10\text{mA}$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$		4.0		pF
Noise figure	NF	$V_{CB} = -6\text{V}$ , $I_E = 0.3\text{mA}$ , $f = 100\text{Hz}$ , $R_G = 10\text{K}\Omega$			20	dB

■  $h_{FE}$  Classification

Marking	ME	MF	MG
$h_{FE}$	150~300	250~500	400~800